

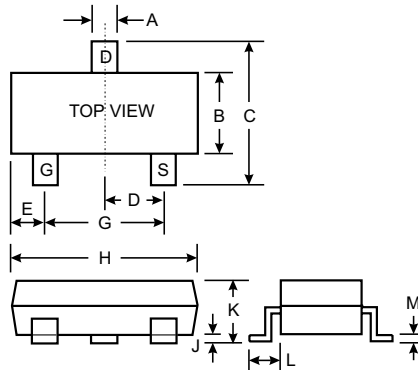
**N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Features**

- Extremely Low On-Resistance:  
170mΩ @  $V_{GS} = 4.5V$
- High Drain Current: 1.1A
- Ideal for Notebook Computer, Portable Phone, PCMCIA Cards, and Battery Powered Circuits

**Mechanical Data**

- Case: SC-59, Molded Plastic
- Case Material - UL Flammability Rating Classification 94V-0
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagrams
- Weight: 0.008 grams (approx.)
- Ordering Information, See Sheet 2



SC-59		
Dim	Min	Max
A	0.30	0.50
B	1.40	1.80
C	2.50	3.00
D	0.85	1.05
E	0.30	0.70
G	1.70	2.10
H	2.70	3.10
J	—	0.10
K	1.00	1.40
L	0.55	0.70
M	0.10	0.35
All Dimensions in mm		

**Maximum Ratings** @  $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	DMN100	Units
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	$\pm 1.1$ $\pm 4.0$	A
Total Power Dissipation	$P_d$	500	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250	K/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

Notes: 1. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

## Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 1)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0 10	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V @ T <sub>j</sub> = 25°C @ T <sub>j</sub> = 125°C
Gate-Body Leakage	I <sub>GSS</sub>	—	—	± 100	nA	V <sub>GS</sub> = ± 12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 1)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	3.0	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.0mA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	0.170 0.240	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.5A V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.0A
Forward Transconductance	g <sub>FS</sub>	1.3	2.4	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.5A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	150	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	90	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	30	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	5.5	—	nC	V <sub>DS</sub> = 24V, I <sub>D</sub> = 1.0A, V <sub>GS</sub> = 10V
Gate-to-Source Charge	Q <sub>gs</sub>	—	0.8	—	nC	
Gate-to-Drain Charge	Q <sub>gd</sub>	—	1.3	—	nC	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	10	—	ns	V <sub>DD</sub> = 10V, I <sub>D</sub> = 0.5A, V <sub>GS</sub> = 5.0V, R <sub>GEN</sub> = 50Ω
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	25	—	ns	
Turn-On Rise Time	t <sub>r</sub>	—	15	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	45	—	ns	
<b>SOURCE- DRAIN RATINGS (BODY DIODE)</b>						
Continuous Source Current	I <sub>S</sub>	—	—	0.54	A	—
Pulse Source Current	I <sub>SM</sub>	—	—	4.0	A	—
Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	I <sub>F</sub> = 1.0A, V <sub>GS</sub> = 0V
Reverse Recovery Time	t <sub>rr</sub>	—	35	—	ns	I <sub>F</sub> = 1.0A, di/dt = 50A/μs

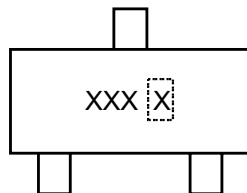
Notes: 1. Pulse width ≤ 300μs, duty cycle ≤ 2%.

## Ordering Information (Note 2)

Device	Packaging	Shipping
DMN100-7	SC-59	3000/Tape & Reel

Notes: 2. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



XXX = Product Type Marking Code  
 X = Assembly Lot No.  
 [0-9, A-Z, except G, I, J, O, Q, W]

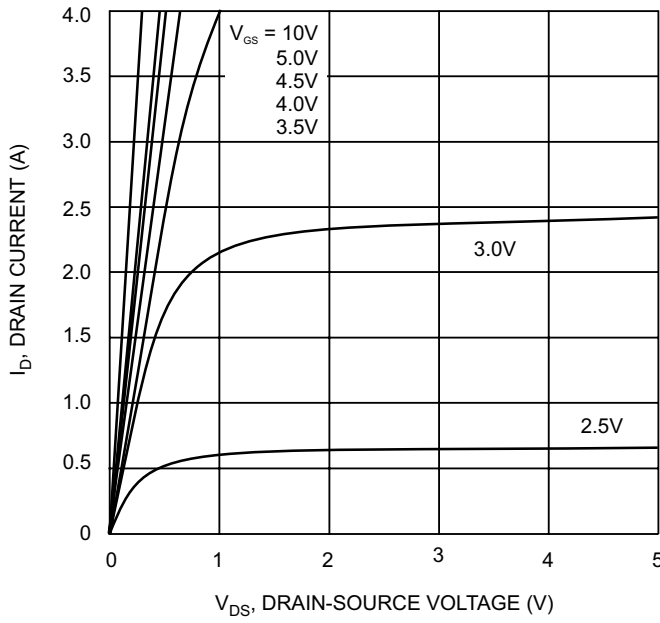


Fig. 1 On-Region Characteristics

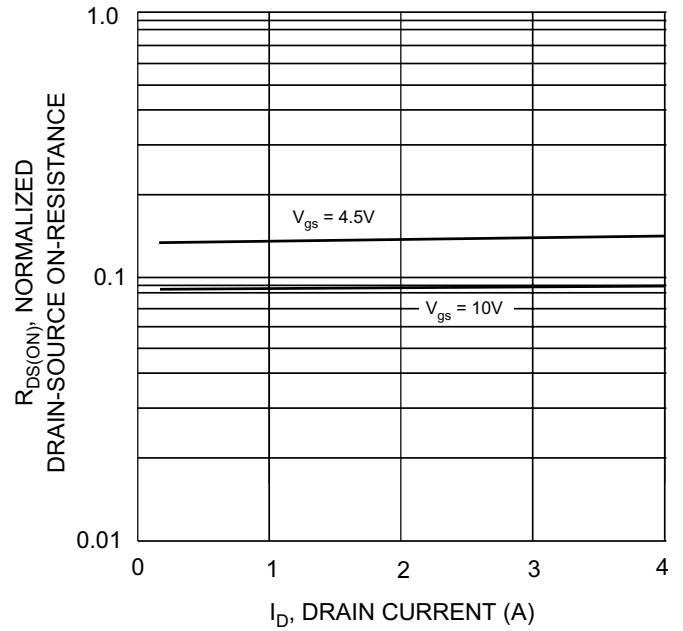


Fig. 2 On-Resistance vs Drain Current

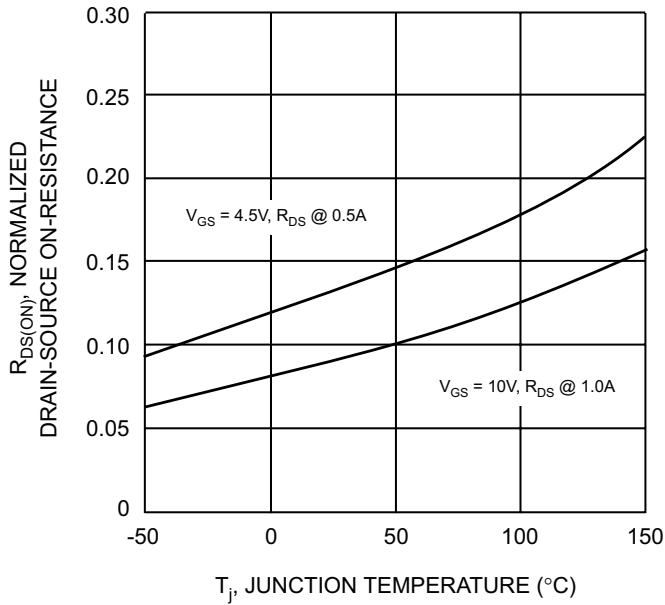


Fig. 3 On-Resistance vs Junction Temperature

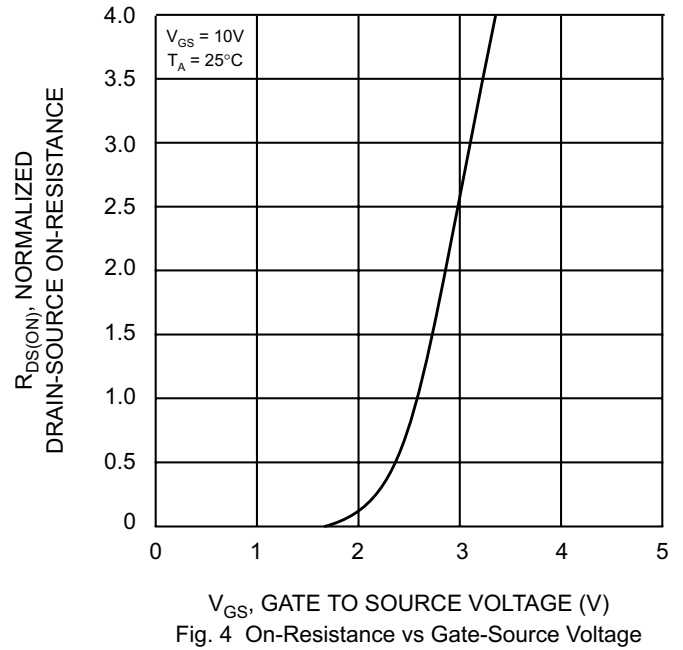


Fig. 4 On-Resistance vs Gate-Source Voltage